

74AUP2G79-Q100

Low-power dual D-type flip-flop; positive-edge trigger

Rev. 1 — 11 June 2013

Product data sheet

1. General description

The 74AUP2G79-Q100 provides the dual positive-edge triggered D-type flip-flop. Information on the data input (nD) is transferred to the nQ output on the LOW-to-HIGH transition of the clock pulse (nCP). The nD input must be stable one set-up time prior to the LOW-to-HIGH clock transition for predictable operation.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$
- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - ◆ JESD8-12 (0.8 V to 1.3 V)
 - ◆ JESD8-11 (0.9 V to 1.65 V)
 - ◆ JESD8-7 (1.2 V to 1.95 V)
 - ◆ JESD8-5 (1.8 V to 2.7 V)
 - ◆ JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - ◆ MIL-STD-883, method 3015 Class 3A. Exceeds 5000 V
 - ◆ HBM JESD22-A114F Class 3A. Exceeds 5000 V
 - ◆ MM JESD22-A115-A exceeds 200 V ($C = 200\text{ pF}$, $R = 0\text{ }\Omega$)
- Low static power consumption; $I_{CC} = 0.9\text{ }\mu\text{A}$ (maximum)
- Latch-up performance exceeds 100 mA per JESD78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot $< 10\text{ }\%$ of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation



3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74AUP2G79DC-Q100	−40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1

4. Marking

Table 2. Marking codes

Type number	Marking code ^[1]
74AUP2G79DC-Q100	p79

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram

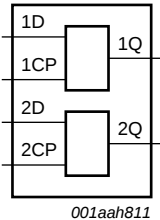


Fig 1. Logic symbol

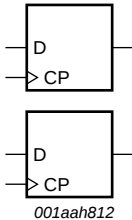
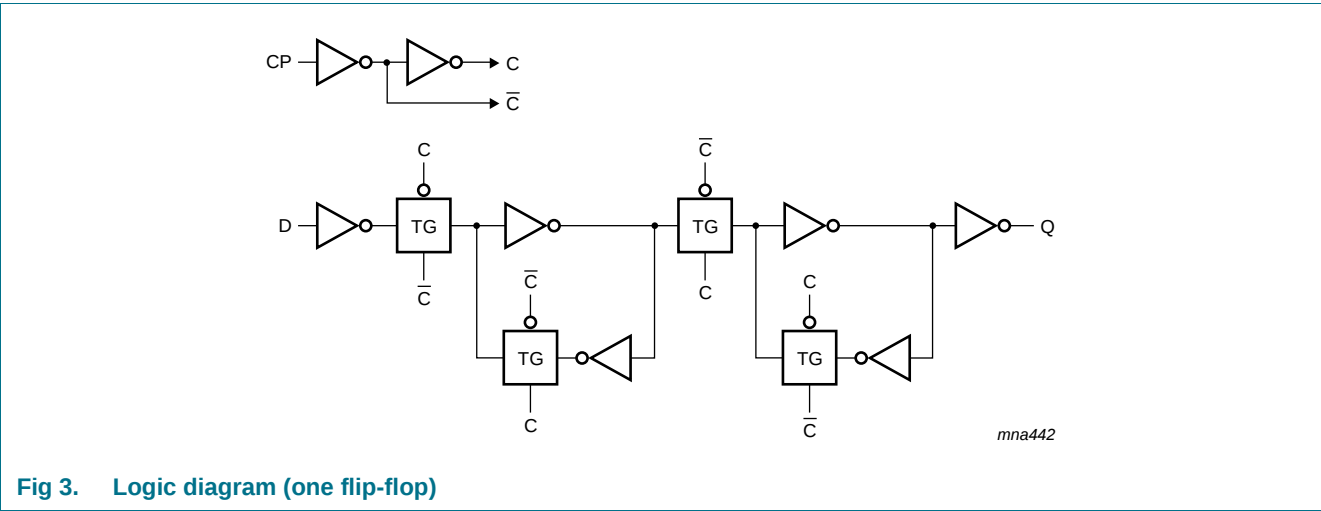


Fig 2. IEC logic symbol



6. Pinning information

6.1 Pinning

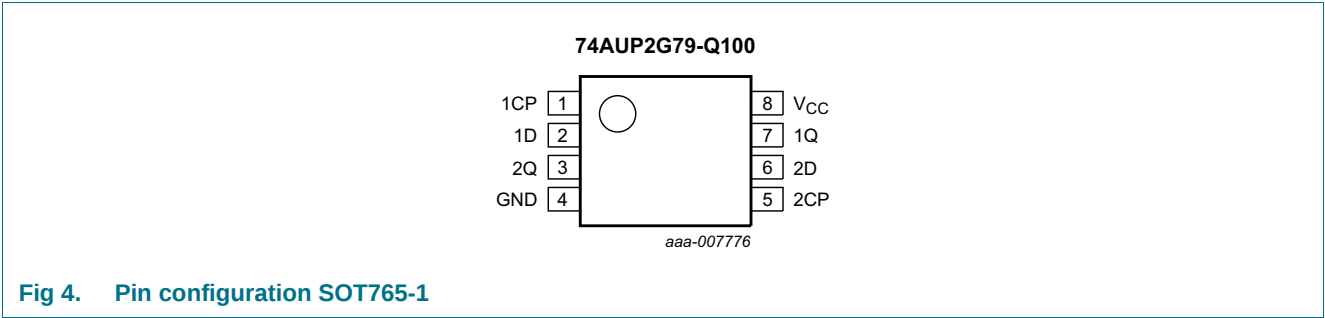


Fig 4. Pin configuration SOT765-1

6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1CP, 2CP	1, 5	clock pulse input
1D, 2D	2, 6	data input
GND	4	ground (0 V)
1Q, 2Q	7, 3	data output
V _{CC}	8	supply voltage

7. Functional description

Table 4. Function table^[1]

Input		Output
nCP	nD	nQ
↑	L	L
↑	H	H
L	X	q

[1] H = HIGH voltage level;
L = LOW voltage level;
↑ = LOW-to-HIGH CP transition;
X = don't care;
q = lower case letter indicates the state of referenced input, one set-up time prior to the LOW-to-HIGH CP transition.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+4.6	V
I_{IK}	input clamping current	$V_I < 0$ V	-50	-	mA
V_I	input voltage		^[1] -0.5	+4.6	V
I_{OK}	output clamping current	$V_O < 0$ V	-50	-	mA
V_O	output voltage	Active mode and Power-down mode	^[1] -0.5	+4.6	V
I_O	output current	$V_O = 0$ V to V_{CC}	-	±20	mA
I_{CC}	supply current		-	50	mA
I_{GND}	ground current		-50	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C	^[2] -	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For VSSOP8 packages: above 110 °C the value of P_{tot} derates linearly with 8.0 mW/K.

9. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		0.8	3.6	V
V_I	input voltage		0	3.6	V
V_O	output voltage	Active mode	0	V_{CC}	V
		Power-down mode; $V_{CC} = 0$ V	0	3.6	V
T_{amb}	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 0.8$ V to 3.6 V	0	200	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = 25 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.65 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -20 µA; V _{CC} = 0.8 V to 3.6 V	V _{CC} - 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.75 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	1.11	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.32	-	-	V
		I _O = -2.3 mA; V _{CC} = 2.3 V	2.05	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.9	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.72	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.6	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 µA; V _{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.31	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.44	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.31	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.44	V
I _I	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.1	µA
I _{OFF}	power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V	-	-	±0.2	µA
ΔI _{OFF}	additional power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V	-	-	±0.2	µA
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V	-	-	0.5	µA
ΔI _{CC}	additional supply current	per pin; V _I = V _{CC} - 0.6 V; I _O = 0 A; V _{CC} = 3.3 V	[1] -	-	40	µA
C _I	input capacitance	V _{CC} = 0 V to 3.6 V; V _I = GND or V _{CC}	-	0.6	-	pF
C _O	output capacitance	V _O = GND; V _{CC} = 0 V	-	1.3	-	pF

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = -40 °C to +85 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.65 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.35 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = -20 µA; V _{CC} = 0.8 V to 3.6 V	V _{CC} - 0.1	-	-	V
		I _O = -1.1 mA; V _{CC} = 1.1 V	0.7 × V _{CC}	-	-	V
		I _O = -1.7 mA; V _{CC} = 1.4 V	1.03	-	-	V
		I _O = -1.9 mA; V _{CC} = 1.65 V	1.30	-	-	V
		I _O = -2.3 mA; V _{CC} = 2.3 V	1.97	-	-	V
		I _O = -3.1 mA; V _{CC} = 2.3 V	1.85	-	-	V
		I _O = -2.7 mA; V _{CC} = 3.0 V	2.67	-	-	V
		I _O = -4.0 mA; V _{CC} = 3.0 V	2.55	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 µA; V _{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.37	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.35	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.33	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.45	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.33	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.45	V
I _I	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.5	µA
I _{OFF}	power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V	-	-	±0.5	µA
ΔI _{OFF}	additional power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V	-	-	±0.6	µA
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V	-	-	0.9	µA
ΔI _{CC}	additional supply current	per pin; V _I = V _{CC} - 0.6 V; I _O = 0 A; V _{CC} = 3.3 V	[1] -	-	50	µA

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = –40 °C to +125 °C						
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.75 × V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.70 × V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 0.8 V	-	-	0.25 × V _{CC}	V
		V _{CC} = 0.9 V to 1.95 V	-	-	0.30 × V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = –20 µA; V _{CC} = 0.8 V to 3.6 V	V _{CC} – 0.11	-	-	V
		I _O = –1.1 mA; V _{CC} = 1.1 V	0.6 × V _{CC}	-	-	V
		I _O = –1.7 mA; V _{CC} = 1.4 V	0.93	-	-	V
		I _O = –1.9 mA; V _{CC} = 1.65 V	1.17	-	-	V
		I _O = –2.3 mA; V _{CC} = 2.3 V	1.77	-	-	V
		I _O = –3.1 mA; V _{CC} = 2.3 V	1.67	-	-	V
		I _O = –2.7 mA; V _{CC} = 3.0 V	2.40	-	-	V
		I _O = –4.0 mA; V _{CC} = 3.0 V	2.30	-	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}				
		I _O = 20 µA; V _{CC} = 0.8 V to 3.6 V	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.33 × V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.41	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.39	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.36	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.50	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.36	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.50	V
I _I	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.75	µA
I _{OFF}	power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V	-	-	±0.75	µA
ΔI _{OFF}	additional power-off leakage current	V _I or V _O = 0 V to 3.6 V; V _{CC} = 0 V to 0.2 V	-	-	±0.75	µA
I _{CC}	supply current	V _I = GND or V _{CC} ; I _O = 0 A; V _{CC} = 0.8 V to 3.6 V	-	-	1.4	µA
ΔI _{CC}	additional supply current	per pin; V _I = V _{CC} – 0.6 V; I _O = 0 A; V _{CC} = 3.3 V	[1]	-	75	µA

[1] One input at V_{CC} – 0.6 V, other input at V_{CC} or GND.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	Min	Max	
C _L = 5 pF										
t _{pd}	propagation delay	nCP to nQ; see Figure 5 ^[2]								
		V _{CC} = 0.8 V	-	19.7	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	2.6	5.5	11.0	2.4	12.9	2.4	14.2	ns
		V _{CC} = 1.4 V to 1.6 V	2.0	3.8	7.0	1.8	8.1	1.8	9.0	ns
		V _{CC} = 1.65 V to 1.95 V	1.7	3.1	5.4	1.5	6.4	1.5	7.1	ns
		V _{CC} = 2.3 V to 2.7 V	1.4	2.3	4.0	1.1	4.7	1.1	5.2	ns
		V _{CC} = 3.0 V to 3.6 V	1.2	2.0	3.4	0.9	4.0	0.9	4.4	ns
f _{max}	maximum frequency	nCP; see Figure 6								
		V _{CC} = 0.8 V	-	53	-	-	-	-	-	MHz
		V _{CC} = 1.1 V to 1.3 V	-	203	-	170	-	170	-	MHz
		V _{CC} = 1.4 V to 1.6 V	-	347	-	310	-	300	-	MHz
		V _{CC} = 1.65 V to 1.95 V	-	435	-	400	-	390	-	MHz
		V _{CC} = 2.3 V to 2.7 V	-	550	-	490	-	480	-	MHz
		V _{CC} = 3.0 V to 3.6 V	-	619	-	550	-	510	-	MHz
C _L = 10 pF										
t _{pd}	propagation delay	nCP to nQ; see Figure 5 ^[2]								
		V _{CC} = 0.8 V	-	23.1	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.1	6.3	12.3	2.8	14.4	2.8	15.9	ns
		V _{CC} = 1.4 V to 1.6 V	2.5	4.4	8.1	2.2	9.5	2.2	10.5	ns
		V _{CC} = 1.65 V to 1.95 V	2.1	3.6	6.3	1.9	7.5	1.9	8.3	ns
		V _{CC} = 2.3 V to 2.7 V	1.8	2.8	4.7	1.5	5.6	1.5	6.2	ns
		V _{CC} = 3.0 V to 3.6 V	1.7	2.5	4.1	1.3	4.5	1.3	5.0	ns
f _{max}	maximum frequency	nCP; see Figure 6								
		V _{CC} = 0.8 V	-	52	-	-	-	-	-	MHz
		V _{CC} = 1.1 V to 1.3 V	-	192	-	150	-	150	-	MHz
		V _{CC} = 1.4 V to 1.6 V	-	324	-	280	-	230	-	MHz
		V _{CC} = 1.65 V to 1.95 V	-	421	-	310	-	250	-	MHz
		V _{CC} = 2.3 V to 2.7 V	-	486	-	370	-	360	-	MHz
		V _{CC} = 3.0 V to 3.6 V	-	550	-	410	-	360	-	MHz

Table 8. Dynamic characteristics ...continuedVoltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	Min	Max	

C_L = 15 pF

t _{pd}	propagation delay	nCP to nQ; see Figure 5 ^[2]								
		V _{CC} = 0.8 V	-	26.6	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.5	7.1	13.6	3.2	15.6	3.2	17.2	ns
		V _{CC} = 1.4 V to 1.6 V	2.8	5.0	9.2	2.5	10.7	2.5	11.8	ns
		V _{CC} = 1.65 V to 1.95 V	2.4	4.1	7.1	2.2	8.5	2.2	9.4	ns
		V _{CC} = 2.3 V to 2.7 V	2.2	3.2	5.4	1.9	6.3	1.9	7.0	ns
		V _{CC} = 3.0 V to 3.6 V	2.0	2.9	4.5	1.6	5.0	1.6	5.5	ns
f _{max}	maximum frequency	nCP; see Figure 6								
		V _{CC} = 0.8 V	-	50	-	-	-	-	-	MHz
		V _{CC} = 1.1 V to 1.3 V	-	181	-	120	-	120	-	MHz
		V _{CC} = 1.4 V to 1.6 V	-	301	-	190	-	160	-	MHz
		V _{CC} = 1.65 V to 1.95 V	-	407	-	240	-	190	-	MHz
		V _{CC} = 2.3 V to 2.7 V	-	422	-	300	-	270	-	MHz
		V _{CC} = 3.0 V to 3.6 V	-	481	-	320	-	300	-	MHz

C_L = 30 pF

t _{pd}	propagation delay	nCP to nQ; see Figure 5 ^[2]								
		V _{CC} = 0.8 V	-	36.8	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	4.7	9.3	17.3	4.2	23.3	4.2	25.6	ns
		V _{CC} = 1.4 V to 1.6 V	3.8	6.4	11.8	3.3	14.3	3.3	15.7	ns
		V _{CC} = 1.65 V to 1.95 V	3.3	5.3	9.4	3.0	11.3	3.0	12.4	ns
		V _{CC} = 2.3 V to 2.7 V	3.0	4.3	7.0	2.7	8.5	2.7	9.4	ns
		V _{CC} = 3.0 V to 3.6 V	2.8	3.9	5.8	2.6	7.2	2.6	7.9	ns
f _{max}	maximum frequency	nCP; see Figure 6								
		V _{CC} = 0.8 V	-	28	-	-	-	-	-	MHz
		V _{CC} = 1.1 V to 1.3 V	-	128	-	70	-	70	-	MHz
		V _{CC} = 1.4 V to 1.6 V	-	206	-	120	-	110	-	MHz
		V _{CC} = 1.65 V to 1.95 V	-	262	-	150	-	120	-	MHz
		V _{CC} = 2.3 V to 2.7 V	-	269	-	190	-	170	-	MHz
		V _{CC} = 3.0 V to 3.6 V	-	309	-	200	-	190	-	MHz

Table 8. Dynamic characteristics ...continuedVoltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	Min	Max	
C _L = 5 pF, 10 pF, 15 pF and 30 pF										
t _{su}	set-up time	HIGH; nD to nCP; see Figure 6								
		V _{CC} = 0.8 V	-	3.4	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	-	0.8	-	1.5	-	1.5	-	ns
		V _{CC} = 1.4 V to 1.6 V	-	0.5	-	1.0	-	1.0	-	ns
		V _{CC} = 1.65 V to 1.95 V	-	0.5	-	0.9	-	0.9	-	ns
		V _{CC} = 2.3 V to 2.7 V	-	0.4	-	0.7	-	0.7	-	ns
		V _{CC} = 3.0 V to 3.6 V	-	0.4	-	0.6	-	0.6	-	ns
		LOW; nD to nCP; see Figure 6								
		V _{CC} = 0.8 V	-	3.0	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	-	0.9	-	1.6	-	1.6	-	ns
		V _{CC} = 1.4 V to 1.6 V	-	0.6	-	1.0	-	1.0	-	ns
		V _{CC} = 1.65 V to 1.95 V	-	0.5	-	0.9	-	0.9	-	ns
		V _{CC} = 2.3 V to 2.7 V	-	0.5	-	0.9	-	0.9	-	ns
		V _{CC} = 3.0 V to 3.6 V	-	0.7	-	1.0	-	1.0	-	ns
t _h	hold time	nD to nCP; see Figure 6								
		V _{CC} = 0.8 V	-	–1.9	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	-	–0.6	-	0	-	0	-	ns
		V _{CC} = 1.4 V to 1.6 V	-	–0.4	-	0	-	0	-	ns
		V _{CC} = 1.65 V to 1.95 V	-	–0.4	-	0	-	0	-	ns
		V _{CC} = 2.3 V to 2.7 V	-	–0.4	-	0	-	0	-	ns
		V _{CC} = 3.0 V to 3.6 V	-	–0.3	-	0	-	0	-	ns
t _w	pulse width	HIGH or LOW; nCP; see Figure 6								
		V _{CC} = 0.8 V	-	5.6	-	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	-	2.4	-	3.5	-	3.5	-	ns
		V _{CC} = 1.4 V to 1.6 V	-	1.3	-	2.0	-	2.0	-	ns
		V _{CC} = 1.65 V to 1.95 V	-	0.9	-	1.9	-	1.9	-	ns
		V _{CC} = 2.3 V to 2.7 V	-	0.7	-	2.0	-	2.0	-	ns
		V _{CC} = 3.0 V to 3.6 V	-	0.6	-	2.2	-	2.2	-	ns

Table 8. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	Min	Max	
C _{PD}	power dissipation capacitance	f = 1 MHz; V _I = GND to V _{CC}								
		V _{CC} = 0.8 V	-	1.6	-	-	-	-	-	pF
		V _{CC} = 1.1 V to 1.3 V	-	1.7	-	-	-	-	-	pF
		V _{CC} = 1.4 V to 1.6 V	-	1.8	-	-	-	-	-	pF
		V _{CC} = 1.65 V to 1.95 V	-	1.9	-	-	-	-	-	pF
		V _{CC} = 2.3 V to 2.7 V	-	2.3	-	-	-	-	-	pF
		V _{CC} = 3.0 V to 3.6 V	-	2.7	-	-	-	-	-	pF

[1] All typical values are measured at nominal V_{CC}.

[2] t_{pd} is the same as t_{PLH} and t_{PHL}.

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

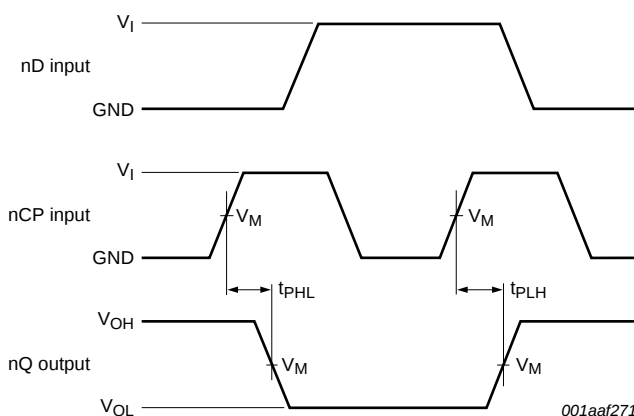
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

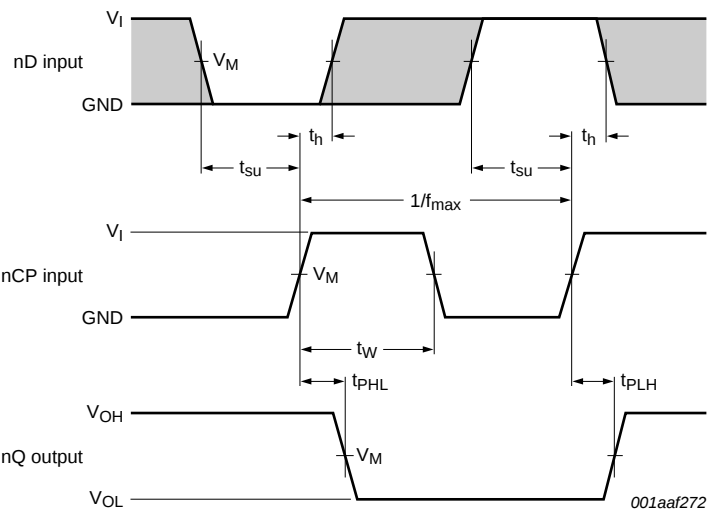
12. Waveforms



Measurement points are given in [Table 9](#).

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 5. The clock input (nCP) to output (nQ) propagation delays

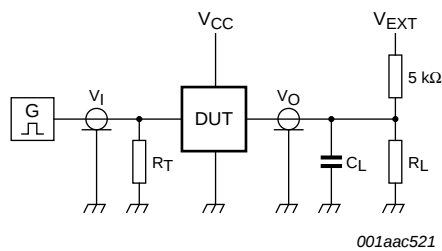


Measurement points are given in [Table 9](#).
Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.
The shaded areas indicate when the input is permitted to change for predictable output performance.

Fig 6. Clock input to output propagation delays, pulse width, set-up times, hold times and maximum frequency

Table 9. Measurement points

Supply voltage	Output	Input		
V_{CC}	V_M	V_M	V_I	$t_r = t_f$
0.8 V to 3.6 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	V_{CC}	≤ 3.0 ns



Test data is given in [Table 10](#).
Definitions for test circuit:
 R_L = Load resistance.
 C_L = Load capacitance including jig and probe capacitance.
 R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.
 V_{EXT} = External voltage for measuring switching times.

Fig 7. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Load		V_{EXT}		
V_{CC}	C_L	R_L [1]	t_{PLH} , t_{PHL}	t_{PZH} , t_{PHZ}	t_{PZL} , t_{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times, $R_L = 5\text{ k}\Omega$. For measuring propagation delays, set-up and hold times and pulse width, $R_L = 1\text{ M}\Omega$.

13. Package outline

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

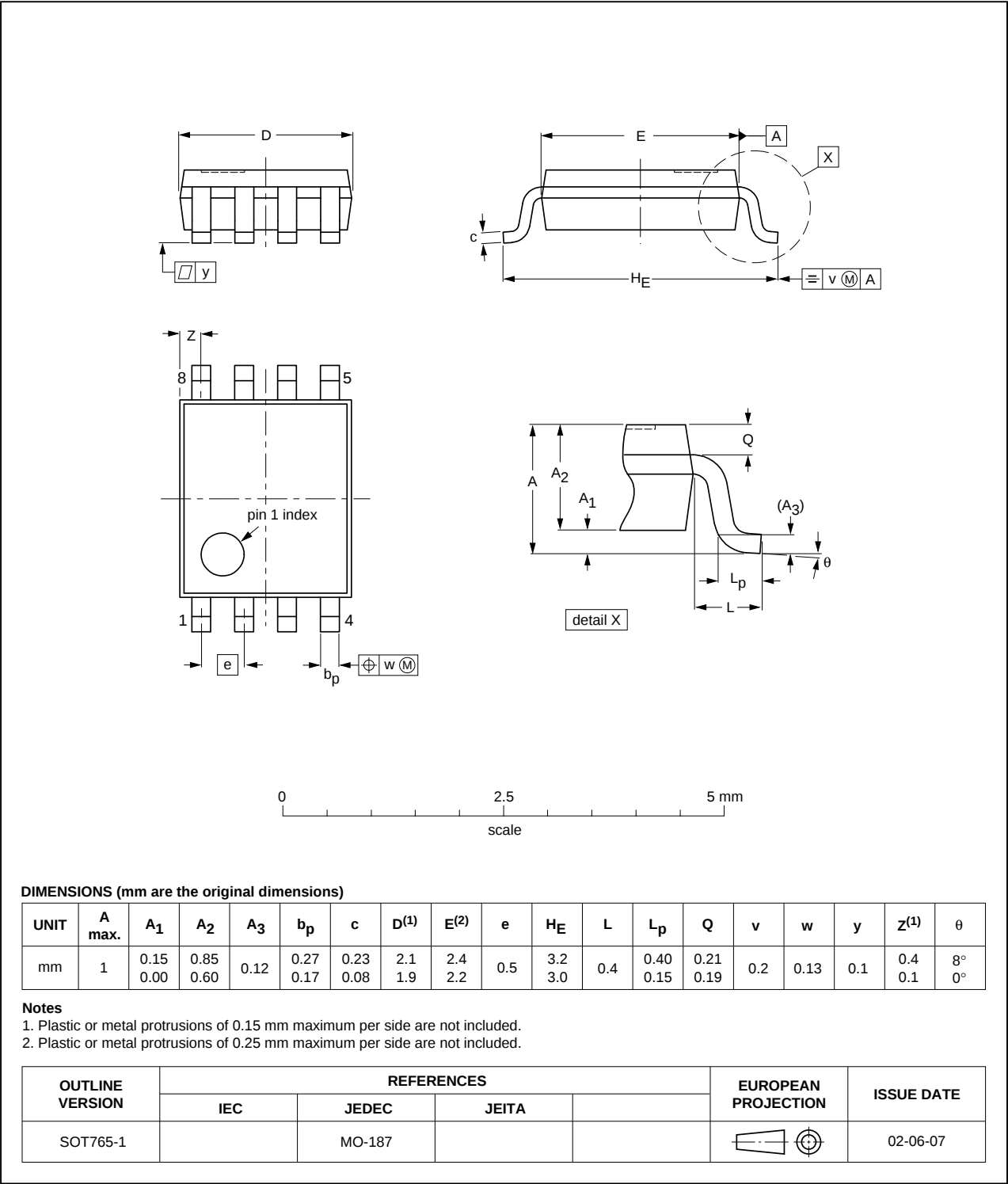


Fig 8. Package outline SOT765-1 (VSSOP8)

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MIL	Military
MM	Machine Model

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP2G79_Q100 v.1	20130611	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[2] The term 'short data sheet' is explained in section "Definitions".

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